DISCRETE SEMICONDUCTORS

DATA SHEET



PESD5V2S18UESD protection array

Product data sheet 2003 Apr 28



ESD protection array

PESD5V2S18U

FEATURES

- Uni-directional ESD protection of up to 18 lines
- Maximum peak reverse power: $P_{PP} = 100 \text{ W}$ at $t_p = 8/20 \mu \text{s}$
- Low clamping voltage:
 V_{CL} = 12 V max. at I_{ZSM} = 10 A
- Low leakage current:
 I_R = 100 nA typ. at V_{RWM} = 5.2 V
- IEC 61000-4-2, level 4 (ESD);
 15 kV (air) and 8 kV (contact).

APPLICATIONS

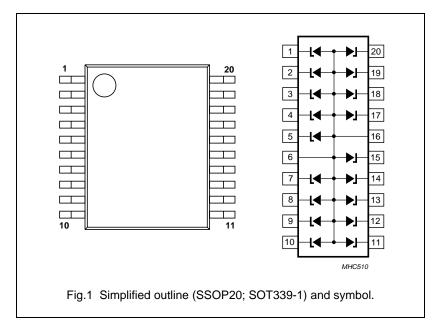
- · Printer parallel ports
- · Computers and peripherals
- · Communication systems.

DESCRIPTION

Monolithic ESD protection device designed to protect up to 18 transmission or data lines from the damage caused by electrostatic discharge (ESD) and surge pulses.

PINNING

PIN	DESCRIPTION			
1 to 5	cathode (k1 to k5)			
6 and 16	common anode (a1; a2)			
7 to 15	cathode (k6 to k14)			
17 to 20	cathode (k15 to k18)			



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{PP}	non-repetitive peak reverse current	t _p = 8/20 μs	_	10	Α
P _{PP}	non-repetitive peak reverse power dissipation	$t_p = 8/20 \ \mu s$	_	100	W
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-65	+150	°C
	electrostatic discharge voltage	IEC 61000-4-2 (contact discharge)	30	_	kV
		HBM MIL-Std 883	10	-	kV

ESD standards compliance

IEC 61000-4-2, level 4 (ESD)	>15 kV (air); >8 kV (contact)
HBM MIL-Std 883, class 3	>4 kV

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	one or more diodes loaded	135	K/W

Note

1. Refer to SOT339-1 standard mounting conditions.

ELECTRICAL CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V _{RWM}	crest working reverse voltage		_	-	5.2	V
I _R	reverse current	V _{RWM} = 5.2 V	_	0.1	1	μΑ
V _{CL}	clamping voltage	$I_{ZSM} = 3 \text{ A}; t_p = 8/20 \mu\text{s}; \text{ see Fig.5}$	_	_	8	V
		$I_{ZSM} = 10 \text{ A}; t_p = 8/20 \mu\text{s}; \text{ see Fig.5}$	_	_	12	V
V_{BR}	breakdown voltage	$I_Z = 5 \text{ mA}$	6.4	6.8	7.2	V
r _{diff}	differential resistance	$I_Z = 1 \text{ mA}$	_	_	40	Ω
		$I_Z = 5 \text{ mA}$	_	_	8	Ω
C_d	diode capacitance	$V_R = 0$; f = 1 MHz; see Fig.4	_	100	_	pF

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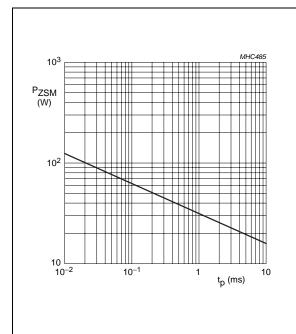


Fig.2 Maximum non-repetitive peak reverse power as a function of pulse duration.

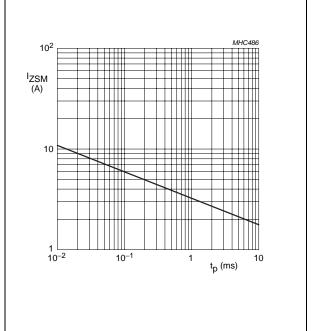


Fig.3 Maximum non-repetitive peak reverse current as a function of pulse duration.

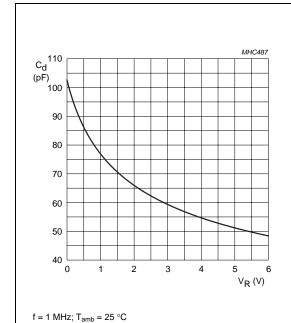


Fig.4 Diode capacitance as a function of reverse voltage; typical values.

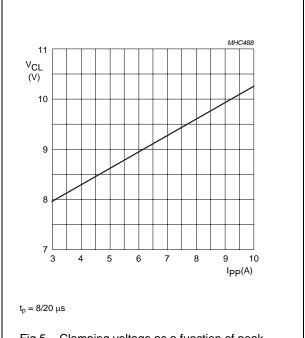
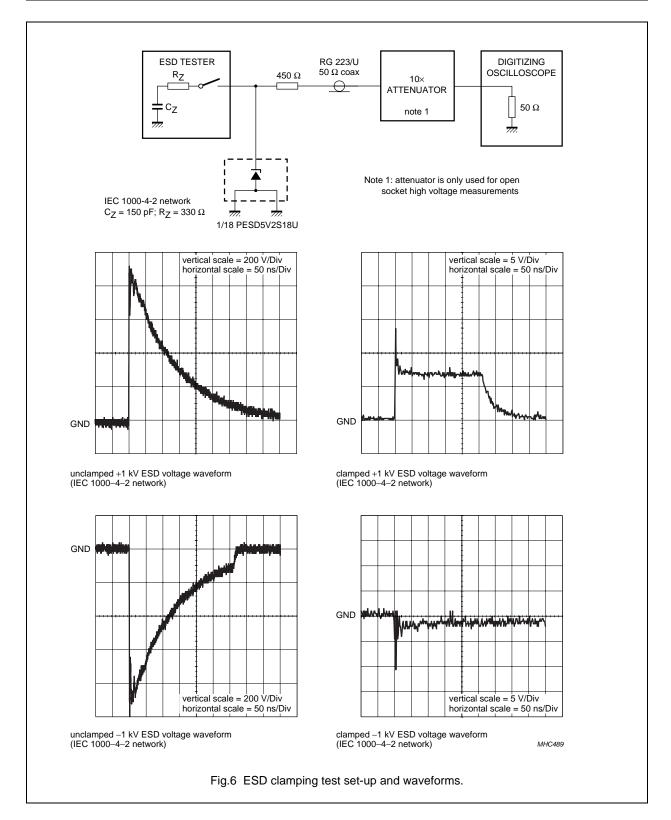


Fig.5 Clamping voltage as a function of peak reverse pulse current; typical values.

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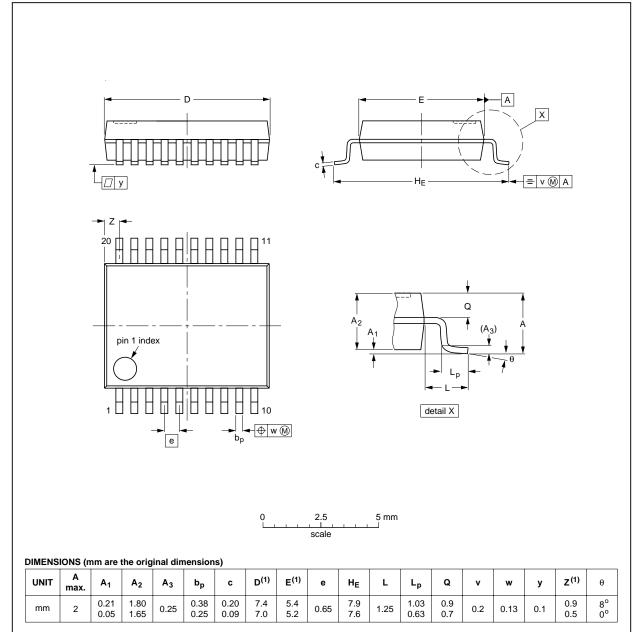
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PACKAGE OUTLINE

SSOP20: plastic shrink small outline package; 20 leads; body width 5.3 mm

SOT339-1



Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

OUTLINE	REFERENCES			EUROPEAN	ISSUE DATE	
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE
SOT339-1		MO-150			$ \ \ \bigoplus $	99-12-27 03-02-19

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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Customer notification

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